

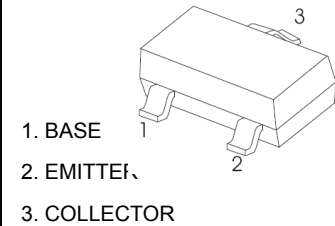
## TRANSISTOR(PNP)

## FEATURES

- Complimentary to S8050
- Collector current:  $I_C=0.5A$

MARKING : 2TY

## SOT-23

MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

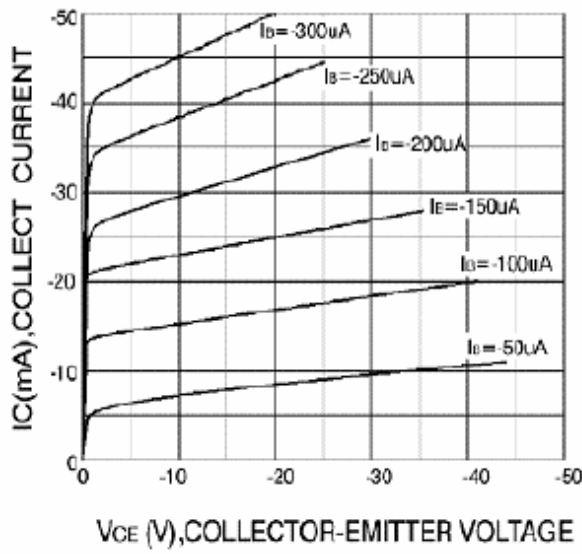
Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.5	A
$P_C$	Collector Power Dissipation	0.3	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$  unless otherwise specified)

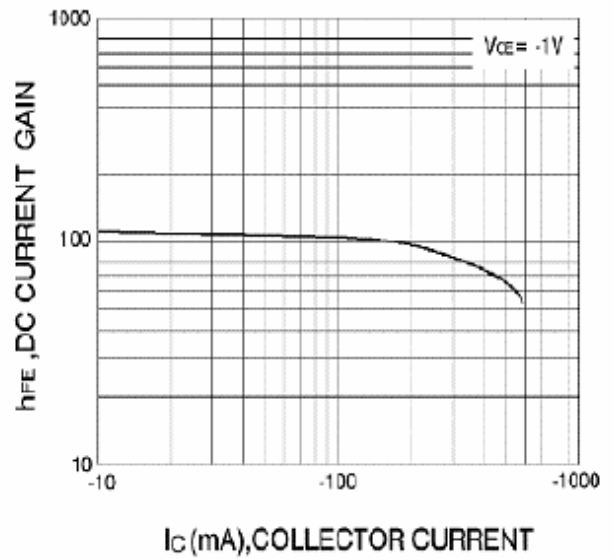
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B=0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40\text{V}, I_E=0$		-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3\text{V}, I_C=0$		-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	120	400	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -500\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.2	V
Transition frequency	$f_T$	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f=30\text{MHz}$	150		MHz

CLASSIFICATION OF  $h_{FE(1)}$ 

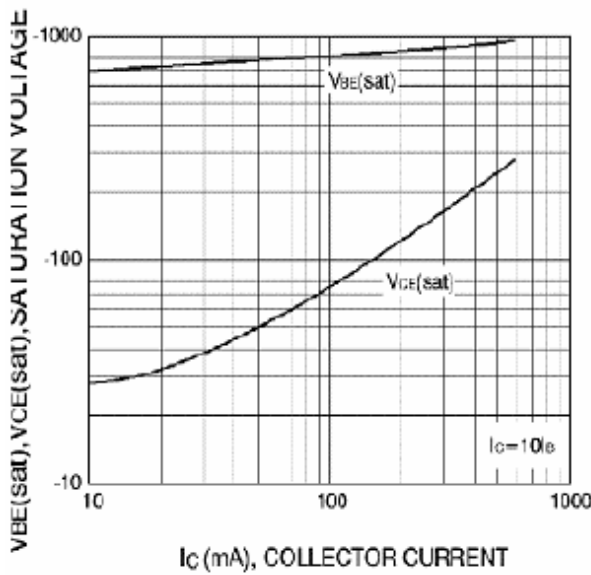
Rank	L	H
Range	120-200	200-350



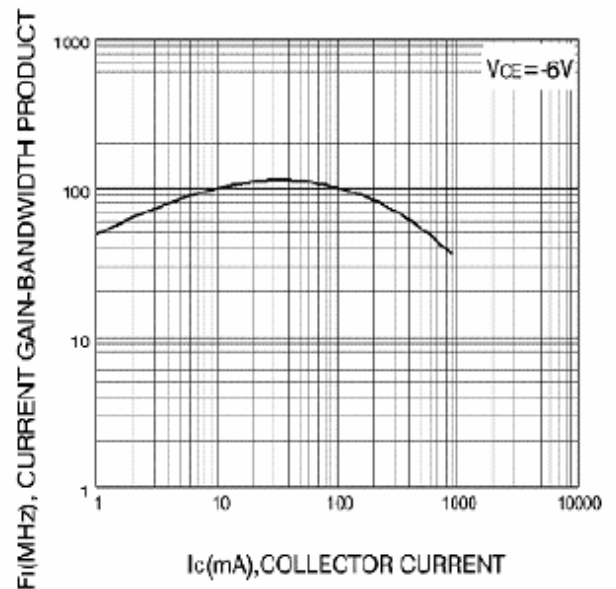
Static Characteristic



DC current Gain



Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product